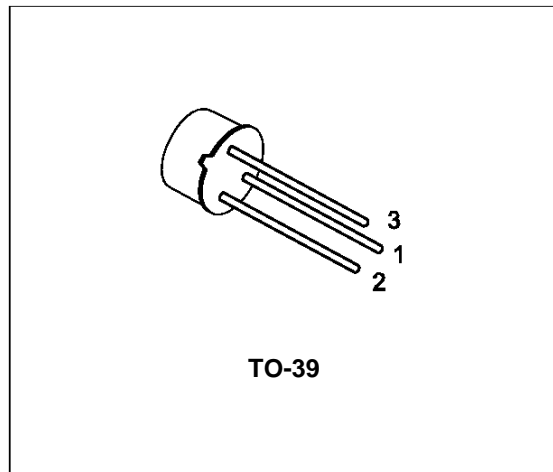
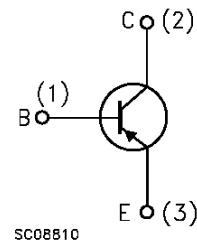


GENERAL PURPOSE TRANSISTORS

DESCRIPTION

The BC161 is a silicon planar epitaxial PNP transistors in Jedec TO-39 metal case. They are particularly designed for audio amplifiers and switching application up to 1A.

The complementary NPN type is the BC141.


INTERNAL SCHEMATIC DIAGRAM

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage ($I_E = 0$)	-60	V
V_{CE0}	Collector-Emitter Voltage ($I_B = 0$)	-60	V
V_{EB0}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-1	A
I_B	Base Current	-0.1	A
P_{tot}	Total Dissipation at $T_{amb} \leq 45\text{ }^\circ\text{C}$ at $T_{case} \leq 45\text{ }^\circ\text{C}$	0.65	W
		3.7	W
T_{stg}	Storage Temperature	-55 to 175	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$

BC161

THERMAL DATA

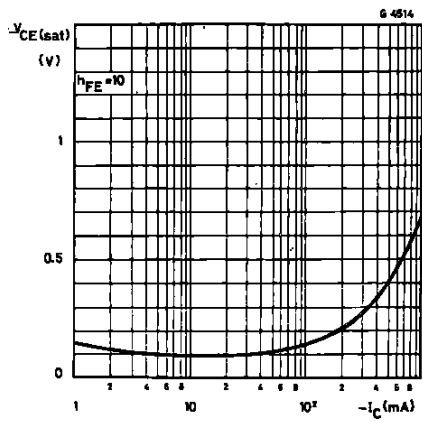
$R_{thj-case}$	Thermal Resistance Junction-Case	Max	35	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	200	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

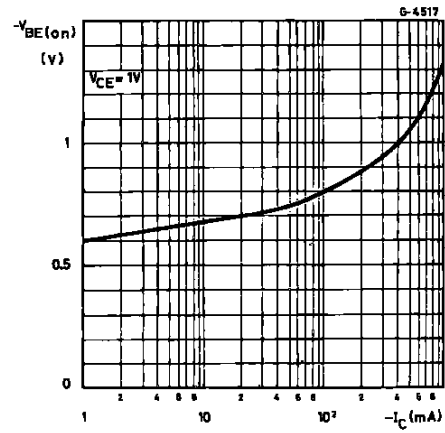
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = -60 V$ $V_{CE} = -60 V$ $T_{amb} = 150^{\circ}C$			-100 -100	nA μA
$V_{(BR)CBO}^*$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = -100 \mu A$	-60			V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = -10 mA$	-60			V
$V_{(BR)EBO}^*$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = -100 \mu A$	-5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = -100 mA$ $I_B = -10 mA$ $I_C = -500 mA$ $I_B = -50 mA$ $I_C = -1 A$ $I_B = -100 mA$		-0.1 -0.35 -0.6		V V V
$V_{BE(on)}^*$	Base-Emitter On Voltage	$I_C = -1 A$ $V_{CE} = -1 V$		-1	-1.7	V
h_{FE}^*	DC Current Gain	$I_C = -100 \mu A$ $V_{CE} = -1 V$ for BC161 for BC161 Gr. 6 for BC161 Gr. 10 for BC161 Gr. 16 $I_C = -100 mA$ $V_{CE} = -1 V$ for BC161 for BC161 Gr. 6 for BC161 Gr. 10 for BC161 Gr. 16 $I_C = -1 A$ $V_{CE} = -1 V$ for BC161 for BC161 Gr. 6 for BC161 Gr. 10 for BC161 Gr. 16		110 46 80 120 40 40 63 100 26 15 20 30	250 100 160 250	
f_T	Transition Frequency	$I_C = -50 mA$ $V_{CE} = -10 V$	50			MHz
C_{CBO}	Collector Base Capacitance	$I_E = 0$ $V_{CB} = -20 V$ $f = 1 MHz$		15	30	pF
C_{EBO}	Emitter Base Capacitance	$I_C = 0$ $V_{CB} = -0.5 V$ $f = 1 MHz$			180	pF
t_{on}	Turn-on Time	$I_C = -100 mA$ $I_{B1} = -5 mA$			500	ns
t_{off}	Turn-off Time	$I_C = -100 mA$ $I_{B1} = I_{B2} = -5 mA$			650	ns

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 1\%$

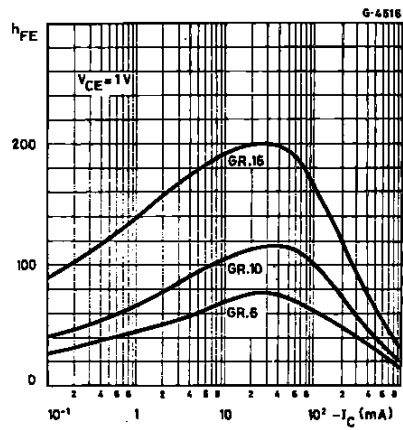
Collector-emitter Saturation Voltage.



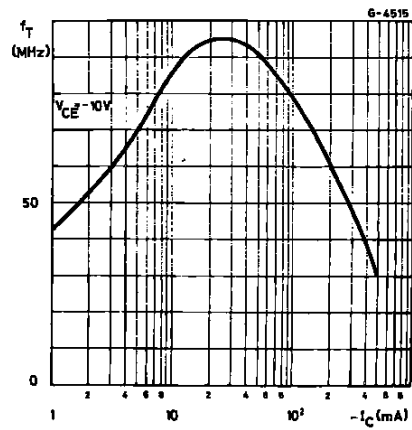
Base-emitter Voltage.



DC Current Gain.

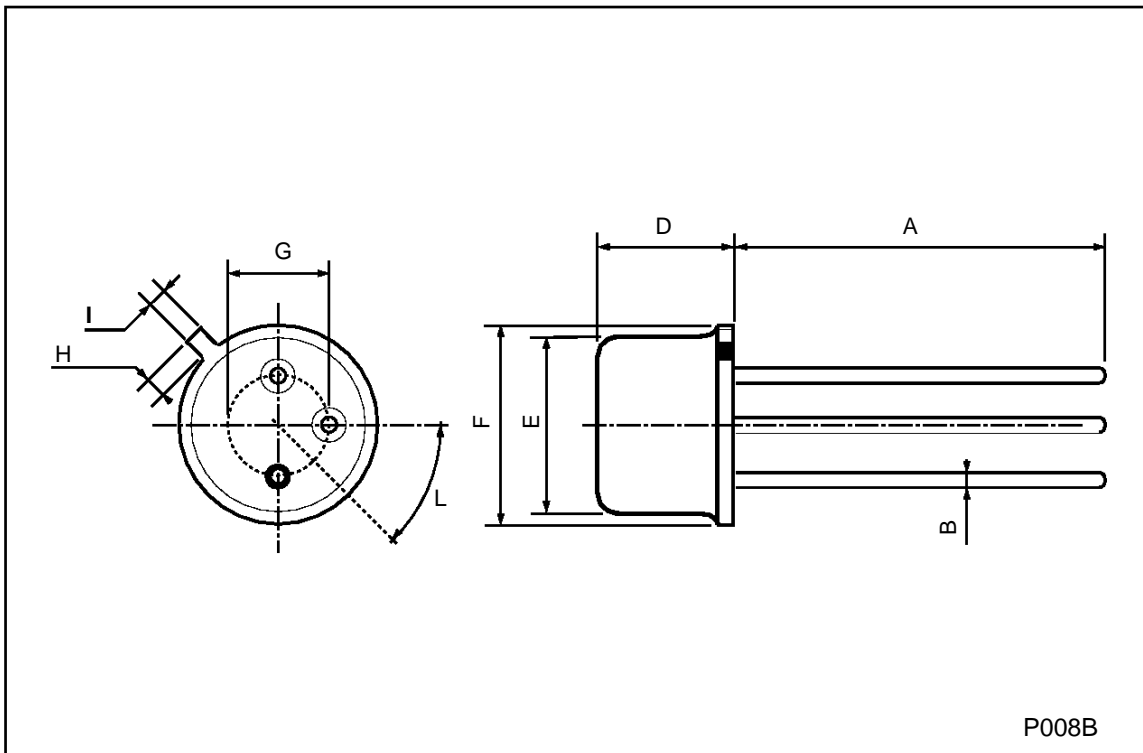


Transition Frequency.



TO-39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



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